

FORM PTO 1449 (modified)				ATTY DOCKET NO. <b>03500.017774</b>		APPLICATION NO <b>10/535,452</b>	
U. S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE				APPLICANTS <b>MIKI OGAWA, ET AL.</b>			
LIST OF REFERENCES CITED BY APPLICANT(S) (Use several sheets if necessary)				FILING DATE <b>May 19, 2005</b>		GROUP <b>1765</b>	
Submitted to the PTO: November 30, 2007							
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*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
/DD/		5,244,828	09/1993	Okada, et al.	437	81	
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		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES/NO/ OR ABSTRACT
/DD/		5-55545	03/1993	Japan			Abstract
/DD/		0 851 506	07/1998	Europe			
/DD/		11-31862	02/1999	Japan			Abstract
/DD/		11-251334	09/1999	Japan			Abstract
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/DD/		M. Jacobs, et al., "Unbalanced Magnetron Sputtered Si-Al Coatings: Plasma Conditions and Film Properties Versus Sample Bias Voltage", Surface and Coatings Technology, 116-119, pp. 735-741 (1999).					
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EXAMINER /Duy Vu Deo/ (02/19/2008)				DATE CONSIDERED			

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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/DD/		2001-261376	09/2001	Japan			Abstract
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/DD/		WO 01/71394	09/2001	PCT			No
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/DD/		2-139714	05/1990	Japan			Abstract
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